

DESIGN AND FABRICATION OF SWNT-FET BASED
BIOSENSOR

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DESIGN AND FABRICATION OF SWNT-FET BASED BIOSENSOR

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*This thesis is dedicated to my beloved wife, family and my supervisor as
mentor and friend*

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TABLE OF CONTENTS

	PAGES
DECLARATION	ii
APPROVAL AND DECLARATION SHEET	ii
DEDICATION	iv
ACKNOWLEDGEMENTS	v
TABLE OF CONTENTS	vi
LIST OF FIGURES	xii
LIST OF TABLES	xvii
LIST OF ABBREVIATIONS	xviii
LIST OF SYMBOLS	xx
LIST OF APPENDICES	xxii
ABSTRAK	xxiii
ABSTRACT	xxiv

CHAPTER ONE: INTRODUCTION

1.1	Research background	1
1.2	Problem Statement	3
1.3	Objectives	3
1.4	Project Scope	4
1.5	Thesis Overview	5

CHAPTER TWO: CARBON NANOTUBE BASED BIOSENSOR

2.1	Carbon nanotube	7
2.2	Structure and characterization of carbon nanotube	8
2.2.1	Chirality	10
2.2.2	Diameter	11
2.2.3	Number of walls	12
2.3	Biosensor concept	12
2.4	Biomolecule interaction with carbon nanotube	15
2.5	Carbon nanotube FET for medical diagnostics application	16
2.6	AC Dielectrophoresis	18
2.7	SWNT-FET	19
2.8	Ballistic Transport	21
2.9	Chapter Summary	23

CHAPTER THREE: SWNT-FET DESIGN AND PROCESS FABRICATION

3.1	Introduction	25
3.2	Mask Design	26
3.2.1	Mask 1 – Alignment mark and gate formation	26
3.2.2	Mask 2 – Insulation Layer	28
3.2.3	Mask 3 – Source and Drain formation	29
3.2.4	Mask 4 – Test channel	31
3.2.5	Actual Chrome Mask	33
3.3	Result	34
3.4	Countermeasures and actions taken	35
3.5	Process Modules for SWNT-FET Fabrication	36
3.5.1	Thermal Oxidations Modules	37
3.5.2	Conventional Lithography Module	38
3.5.3	Lift-Off Lithography Module	41
3.5.4	Wet Etch Module	43
3.5.5	Thin Films Depositions Modules	45

3.6	Fabrication process	47
3.6.1	Device fabrication	47
3.6.2	Alignment mark and gate fabrication	48
3.6.3	Insulation layer fabrication	54
3.6.4	Source and drain fabrication	59
3.6.5	Carbon nanotube placement and integration by AC Dielectrophoresis.	63
3.7	Result	69
3.7.1	Gate formation	69
3.7.2	Oxidation	71
3.7.3	Source and Drain formation	71
3.7.4	Single Walled Carbon Nanotubes	74
3.7.5	AC dielectrophoresis	75
3.7.6	Morphological Characterization	78
3.8	Chapter Summary	81

CHAPTER FOUR: FUNCTIONAL TESTING AND CHARACTERIZATION OF

SWNT-FET

4.1	Introduction	84
4.2	Functional Testing of SWNT-FET	85
	4.2.1 Measurement Set-Up	85
4.3	Results and Discussion	87
	4.3.1 Single Walled Carbon Nanotube as MOSFET	87
	4.3.2 Types of graph characterization for SWNT-FET as biosensor	91
4.4	Chapter Summary	93

CHAPTER FIVE: CONCLUSION AND FUTURE WORK

7.1	Summary of the Thesis	94
7.2	Conclusions	95
7.3	Suggestions for Future Work	96

REFERENCES	97
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APPENDIX A:	LIST OF PUBLICATIONS	104
APPENDIX B:	DRAFT PLANS OF MASK DESIGN	106
APPENDIX C:	DRAFT PLANS OF FABRICATION AND OPTIMIZATIONS	111
APPENDIX C:	SPECIAL CHEMICALS FOR LIFT-OFF LITHOGRAPHY	120

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LIST OF FIGURES

FIGURE		PAGE
Figure 1	DNA detection on semiconducting carbon nanotube.....	2
Figure 2.1	Carbon allotropies. Clockwise from top left: diamond, graphite, C60 buckyball, nanotube.....	8
Figure 2.2	SEM images of a single walled nanotube integrated with metal pads.....	9
Figure 2.3	Schematic diagram showing the main components of a Biosensor.....	13
Figure 2.4	The structural models of the (5, 5) CNT composed of 48 unit cells (1), distorted chain of the single-stranded DNA composed of 36 nucleotides (2) and their complex (5, 5) CNT at DNA (3).....	16
Figure 2.5	DNA detection on semiconducting carbon nanotube.....	18
Figure 2.6	Ids-Vds curve of p-type SWNT-FET.....	20
Figure 2.7	Band diagram of ON state.....	21
Figure 2.8	Conductance versus gate voltage curve.....	23

LIST OF FIGURES

FIGURE		PAGE
Figure 3.1	Alignment mark and gate dimension for Mask 1.....	27
Figure 3.2	Alignment mark and gate dimension for each single chip.....	28
Figure 3.3	Dimension of insulation layer mask 2.....	29
Figure 3.4	Dimension of metal pads mask 3.....	30
Figure 3.5	Zoomed dimension of metal pads source and drain.....	31
Figure 3.6	Dimension of test channel.....	32
Figure 3.7	Dimension of test channel on top of SWNT.....	32
Figure 3.8	Actual chrome mask.....	33
Figure 3.9	High Power Microscope image of gate without narrow gate.....	34
Figure 3.10	Illustrations of the conversion of top gated to back gated device.....	36
Figure 3.11	Oxidation Furnace Module.....	37
Figure 3.12	Filmetrics F20 Thin Film Analyzer.....	38
Figure 3.13	Photolithography process flow.....	39
Figure 3.14	Wafer Spinner.....	40
Figure 3.15	Hot Plate.....	40

LIST OF FIGURES

FIGURE		PAGE
Figure 3.16	Contact Mask Aligner and Exposure System.....	42
Figure 3.17	Development Bench.....	42
Figure 3.18	Lift-Off process flow.....	43
Figure 3.19	Wet Etch Module.....	44
Figure 3.20	Thermal Evaporator Module.....	45
Figure 3.21	Ambios XP-1 Stylus Surface Profiler.....	46
Figure 3.22	Bare wafer.....	48
Figure 3.23	Resist coating.....	50
Figure 3.24	Pattern transfer and exposure I.....	51
Figure 3.25	Gate metallization.....	52
Figure 3.26	Resist strip and lift-off I.....	53
Figure 3.27	Insulation layer deposition.....	54
Figure 3.28	Pattern transfer and exposure II.....	56
Figure 3.29	Insulation layer pattern and develop.....	58
Figure 3.30	Oxide layer wet etch.....	58

LIST OF FIGURES

FIGURE		PAGE
Figure 3.31	Resist strip.....	59
Figure 3.32	Pattern transfer and exposure III.....	60
Figure 3.33	Source and drain metallization.....	61
Figure 3.34	Resist strip and lift-off II.....	62
Figure 3.35	Simulations of AC Dielectrophoresis method.....	64
Figure 3.36	Dispersed SWNTs.....	65
Figure 3.37	Dropping of SWNTs in Triton X-100 solution.....	66
Figure 3.38	Circuit set up for AC dielectrophoresis.....	67
Figure 3.39	Circuit set up for AC dielectrophoresis.....	68
Figure 3.40	Thickness of gate multilayer metal.....	69
Figure 3.41	Thickness of gate multilayer metal.....	70
Figure 3.42	Final device fabricated image and SEM image.....	72
Figure 3.43	Thickness of gate multilayer metal.....	73
Figure 3.44	Raman spectra of single-walled carbon nanotubes purchased.....	75

LIST OF FIGURES

FIGURE		PAGE
Figure 3.45	Resistance over time graph when AC voltage applied.....	77
Figure 3.46	Schematic diagram of device geometry.....	78
Figure 3.47	SEM image of a full device electrode.....	79
Figure 3.48	Annealed dropping of SWNTs.....	79
Figure 3.49	Close up SEM image of a device small gap between source and drain.....	80
Figure 3.50	The process flow of device fabrication.....	83
Figure 4.1	Finalized carbon nanotube based biosensor device.....	84
Figure 4.2	Semiconductor Characterization System (SCS), Micro Probe Station..	86
Figure 4.3	Keithley 4200 Semiconductor Parameter Analyzer (SPA).....	86
Figure 4.4	Band diagram of ON state.....	88
Figure 4.5	IDS-VDS curves	90
Figure 4.6	Conductance vs VG curves.....	91
Figure 4.7	Current vs Voltage curves.....	92

LIST OF TABLES

TABLE		PAGE
Table 4.1	Parameters of gate metallization.....	54
Table 4.2	Parameters of gate metallization lift off process.....	55
Table 4.3	Parameters of insulation deposition.....	57
Table 4.4	Parameters of gate formation resist coating.....	59
Table 4.5	Parameters of oxide etch and strip resist.....	61
Table 4.6	Parameters of gate formation resist coating.....	63
Table 4.7	Parameters of source and drain metallization.....	65
Table 4.8	Parameters of gate metallization lift off process.....	66
Table 5.1	Resistance over time when AC voltage applied.....	60

LIST OF ABBREVIATIONS

AC	Alternating current
AFM	Atomic force microscope
Al	Aluminum
Au	Gold
BOE	Buffer Oxide Etch
CNT	carbon nanotubes
CNTFET	Carbon nanotube field effect transistor
CV	Capacitance-Voltage
DC	Direct current
DEP	dielectrophoresis
DNA	Deoxyribonucleic acid
FET	Field effect transistor
IV	Current-Voltage
MWNT	Multi-walled carbon nanotubes
NMOS	N-channel MOSFET
O ₂	Oxygen (gaseous)

PMOS	P-channel MOSFET
Pt	Platinum
RBM	Radial breathing mode
RNA	Ribonucleic acid
Rpm	Revolution per minute
SEM	Scanning electron microscope
Si	Silicon
SiO ₂	Silicon dioxide
SPA	Semiconductor Parameter Analyzer
SWNT	Single-walled carbon nanotubes
SWNT-FET	Single-walled carbon nanotubes field effect transistor
STM	Scanning tunneling microscope
TEM	Transmission electron microscope
UV	Ultraviolet

LIST OF SYMBOLS

Symbol	Description	Unit
I_D	Drain current	A
V_D	Drain voltage	V
V_G	Gate voltage	V
V_{TH}	Threshold Voltage	V
W	Width of Area	μm
d	Diameter	μm
L	Length of Area	μm
μ_p	Electron mobility	$\text{cm}^2/\text{V.s}$
C_0	Oxide capacitance per unit area	F/m^2
V_{DSAT}	Drain voltage at saturation	V
ϕ	Work function	eV
ϕ_B	Ohmic contact of p-type	eV
ϕ_M	Work function of metal	eV
e	Electron charge	eV
h	Planck constant	eV.s
E_g	Band gap	eV
χ_s	Work function of semiconductor	eV
G	Conductance	Ω
R	Resistance	Ω

LIST OF SYMBOLS

Symbol	Description	Unit
t_{ox}	Oxide thickness	nm
C_i	Gate insulator capacitance per unit area	F/m ²

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LIST OF APPENDICES

APPENDIX	DESCRIPTION	PAGE
A	LIST OF PUBLICATIONS	106
B	DRAFT PLANS OF MASK DESIGN	108
C	DRAFT PLANS OF FABRICATION AND OPTIMIZATIONS	113
D	SPECIAL CHEMICALS FOR LIFT-OFF LITHOGRAPHY	122

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Rekabentuk dan Fabrikasi biosensor SWNT-FET

Abstrak

Nanotub telah menjana aktiviti penyelidikan yang sengit daripada saintis pelbagai bidang kerana ia mewakili kelas baru bahan-bahan untuk kajian fizik satu dimensi. Nanotub karbon berdinding tunggal (SWNTs) mempunyai banyak sifat-sifat lain yang menarik dan mengagumkan dalam ketiga-tiga aspek iaitu mekanikal, elektrik dan biologi kerana keupayaan nanotub karbon berdinding tunggal (SWNTs) untuk mempamerkan lapisan pemasangan sendiri (SAM). Objektif utama projek ini adalah untuk mereka bentuk, membina dan mencari karbon nanotub biosensor untuk aplikasi diagnostik perubatan untuk masa depan. Pengangkutan elektrik semikonduktor nanotub karbon berdinding tunggal dengan diameter ~ 1.5 nm dan panjangnya berukuran $2 \mu\text{m}$ hingga $6 \mu\text{m}$ untuk aplikasi sebagai pengesanan biomolekul telah disiasat. Transistor kesan medan karbon nanotub berdinding tunggal (SWNT-FET) telah difabrikasikan dengan menggunakan tiga topeng yang telah direka. Pada mulanya backgated transistor kesan medan (FET) telah difabrikasikan dan diikuti dengan pertumbuhan oksida sebagai lapisan penebat. Logam dwilapis bagi platinum, Pt dan emas, Au ditumbuhkan di atas lapisan oksida dan akhirnya diikuti dengan integrasi nanotub karbon berdinding tunggal (SWNTs). Ketebalan oksida yang dicapai adalah ~ 18 nm dan logam dwilapis platinum, Pt berketebalan ~ 10 nm dan emas, berketebalan ~ 90 nm. Integrasi nanotub karbon berdinding tunggal (SWNTs) dengan transistor kesan medan (FET) telah dilakukan dengan menggunakan teknik AC dielectrophoresis nanomanipulation menghasilkan keputusan menggalakkan. Ini telah terbukti melalui Scanning Electron Microscope (SEM). Peranti yang telah difabrikasikan dengan menghasilkan konduktans $G \sim 0.03 \times 4e^2/h$ dan lubang pergerakan $\mu_h \sim 3060 \text{ cm}^2/\text{Vs}$ dalam mod tepu. Peranti ini juga menunjukkan ciri-ciri yang bersamaan dengan konvensional jenis-p logam oksida-semikonduktor FET (MOSFET) melalui graf $I_{\text{DS}}-V_{\text{DS}}$ dan kajian ini menunjukkan ia bergantung kepada nilai voltan gate melalui graf voltan get konduktans. Oleh itu, keputusan ini membuktikan bahawa ia boleh digunakan untuk mengesan biomolekul seperti protein dengan hanya memantau perubahan $I_{\text{DS}}-V_{\text{DS}}$.